Si surfaces - electronic structure and dynamics

Workshop at the Max Born Institute, Berlin-Adlershof, 9-10th September 2005

Friday 9th

13:00 - 14:30  Transport from ECOSS conference location to MBI and welcome

15:00  Theory of the electronic structure of the Si(001) surface revisited, Peter Kratzer (Fritz-Haber-Institute, Berlin, Germany)

15:45  Temperature dependence of single electron dynamics at Si(100), Martin Weinelt (Max-Born-Institute, Berlin, Germany)

16:30  Coffee

17:00  Two-photon photoemission from metallic chains on Si surfaces, Tilman Ruegheimer (Lehrstuhl für Festkörperphysik, Universität Erlangen, Germany)

17:30  Density-dependent carrier dynamics of highly excited Si(111)7x7 dangling bonds, Ulrich Höfer (Fachbereich Physik, Universität Marburg, Germany)

18:15  Electron dynamics of silicon surface states: Second-harmonic hole burning on Si(111)7x7, Markus B. Raschke (Max-Born-Institute, Berlin, Germany)
Saturday 10th

9:15  Non-adiabatic molecular dynamics simulations of Si(001) surfaces, Eckhard Pehlke (Institut für Theoretische Physik und Astrophysik, Universität Kiel, Germany)

10:00  Laser-induced structural instabilities of Si surfaces, Jun'ichi Kanasaki (Osaka University, The Institute of Scientific and Industrial Research, Osaka, Japan)

10:45  Coffee

11:15  Electronic structure of Si(100) at high excitation density, Tanja Gießel (Max-Born-Institute, Berlin, Germany)

11:45  Dynamics of carrier localization and Si-bond rupture on Si surfaces, Katsumi Tanimura (Osaka University, The Institute of Scientific and Industrial Research, Osaka, Japan)

12:30  The future of silicon surfaces – concluding remarks, Thomas Fauster (Lehrstuhl für Festkörperphysik, Universität Erlangen, Germany)